

## Optically-Coupled Isolator

photoelectronic Products

### General Description

The H11A1, H11A2, H11A3 and H11A4 optical isolators are electrical and mechanical replacements for the General Electric series. Optical intercoupling provides a high degree of ac and dc isolation. A capability for continuous operation of the input diode results in a frequency response extending to dc. Connection to the base is also provided for design flexibility.

### Glassolated™

Electrically Equivalent to GE Devices

Pin-for-Pin Equivalent to GE Devices

Availability of Base Pin for Flexible Design

### Absolute Maximum Ratings

#### Maximum Temperature and Humidity

Storage Temperature  $-55^{\circ}\text{C}$  to  $+150^{\circ}\text{C}$

Operating Temperature  $-55^{\circ}\text{C}$  to  $+100^{\circ}\text{C}$

Pin Temperature (Soldering, 5 s)  $260^{\circ}\text{C}$

#### Total Package Power Dissipation

at  $T_A = 25^{\circ}\text{C}$ ,

LED plus Detector

250 mW

Derate Linearly from  $25^{\circ}\text{C}$

$3.3 \text{ mW}/^{\circ}\text{C}$

#### Input Diode

$V_R$  Reverse Voltage 3.0 V

$I_F$  Forward dc Current 60 mA

$I_{pk}$  Peak Forward Current at 1  $\mu\text{s}$  pulse width,

300 pps

3.0 A

$P_D$  Power Dissipation

at  $T_A = 25^{\circ}\text{C}$

$100 \text{ mW}/^{\circ}\text{C}$

Derate Linearly from  $25^{\circ}\text{C}$

$1.33 \text{ mW}/^{\circ}\text{C}$

#### Output Transistor

$V_{CE}$  Collector-to-Emitter

30 V

$V_{CB}$  Collector-to-Base

70 V

$I_C$  Collector Current

100 mA

$P_D$  Power Dissipation

at  $T_A = 25^{\circ}\text{C}$

$150 \text{ mW}$

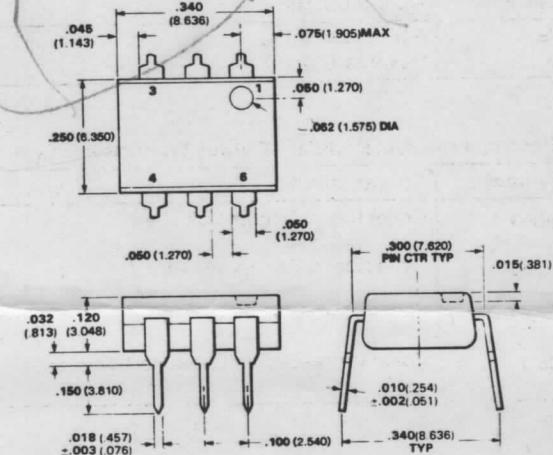
Derate Linearly from  $25^{\circ}\text{C}$

$2.0 \text{ mW}/^{\circ}\text{C}$

AD  
A  
AS  
I

## H11A1, H11A2 H11A3, H11A4

### Package Outline



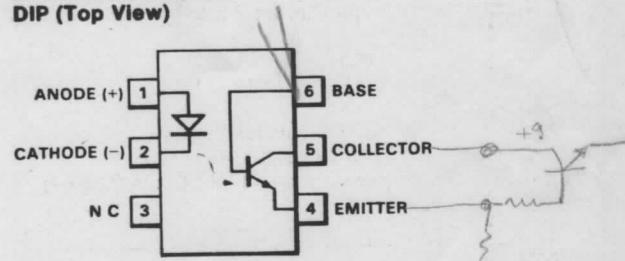
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### Notes

All dimensions in inches bold and millimeters (parentheses)

Tolerance unless specified =  $\pm .015$  ( $\pm .381$ )

### Connection Diagram DIP (Top View)

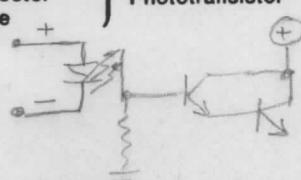


### Pin

1 Anode (+)  
2 Cathode (-) } Input Diode

3 NC

4 Emitter  
5 Collector  
6 Base } Output npn  
Phototransistor



## Typical Electrical Characteristics

H11A1, H11A2  
H11A3, H11A4

## Optically-C Darlington

**Electrical Characteristics—Input Diode  $T_A = 25^\circ\text{C}$**

Symbol	Characteristic	Min	Typ	Max	Units	Test Conditions
$V_F$	Forward Voltage		1.1	1.5	V	$I_F = 10 \text{ mA}$
$I_R$	Reverse Current			10	$\mu\text{A}$	$V_R = 3.0 \text{ V}$

**Electrical Characteristics—Output Transistor  $T_A = 25^\circ\text{C}$**

Symbol	Characteristic	Min	Typ	Max	Units	Test Conditions
$V_{CEO}$	Collector-to-Emitter Voltage	30			V	$I_C = 10 \text{ mA}$ , $I_F = 0$
$V_{CBO}$	Collector-to-Base Voltage	70			V	$I_C = 100 \mu\text{A}$ , $I_F = 0$
$V_{ECO}$	Emitter-to-Collector Voltage	7.0			V	$I_E = 100 \mu\text{A}$ , $I_F = 0$
$I_{CEO}$	Collector-to-Emitter Leakage Current		5.0	50	nA	$V_{CE} = 10 \text{ V}$ , $I_F = 0$

**Electrical Characteristics—Coupled  $T_A = 25^\circ\text{C}$**

Symbol	Characteristic	Min	Typ	Max	Units	Test Conditions
$V_{ISO}$	Isolation Voltage (Note 3) H11A1, H11A3	2500	0.1	0.4	V	Peak
	H11A2, H11A4					Peak
$V_{CE(sat)}$	Collector-to-Emitter Saturation Voltage	1500			V	$I_C = 0.5$ mA, $I_F = 50$ mA
$I_C/I_F(CTR)$	Collector Current Transfer Ratio (Note 1)					$V_{CE} = 10$ V, $I_F = 10$ mA
$R_{IO}$ $C_{IO}$ $t_r, t_f$	H11A1	50			%	
	H11A2, H11A3	20			%	
	H11A4	10			%	
	Input-to-Output Resistance	10 <sup>11</sup>			$\Omega$	$V_{IO} = 500$ V
	Input-to-Output Capacitance		2.0		pF	$f = 1.0$ MHz
	Collector Rise and Fall Times (Note 2)			2.0	$\mu$ s	$I_C = 2.0$ mA, $V_{CE} = 10$ V, $R_L = 100$ $\Omega$

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## Notes

**Notes**

1. Collector current transfer ratio is defined as the ratio of the collector current to the forward bias input current.
2. Rise time is defined as the time for the collector current to rise from 10% to 90% of peak value. Fall time is defined as the time required for the current to decrease from 90% to 10% of peak value.
3. Isolation voltage defined as minimum of 5 s continuous application.

**General Description**  
The H11B1 and H11B2 and mechanical replacement series. Optical intercoupling and dc isolation. A wide range of operation of the input response extending to 1000 cps is also provided for design flexibility.

**Glassolated™  
Electrically Equivalent  
Pin-For-Pin Equivalent  
Availability of Base P**

**Absolute Maximum Ratings**

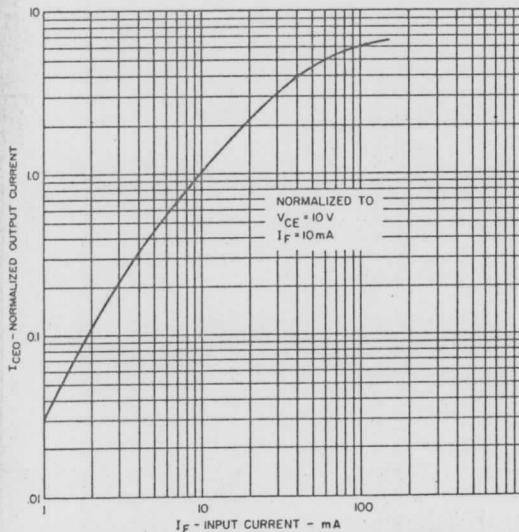
**Maximum Temperature  
Storage Temperature  
Operating Temperature  
Pin Temperature (Solder  
Total Package Power  
at  $T_A = 25^\circ\text{C}$   
LED plus Detector  
Derate Linearly from 2**

<b>Input</b>	<b>Diode</b>
<b>F</b>	Forward dc Current
	Continuous
<b>V<sub>R</sub></b>	Reverse Voltage
<b>V<sub>pk</sub></b>	Peak Forward Current
	(1 $\mu$ s pulse width)
<b>P<sub>D</sub></b>	Power Dissipation
	T <sub>A</sub> = 25°C
	Derate Linearly

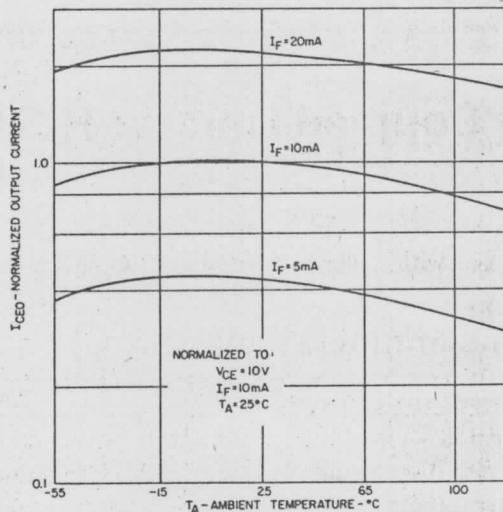
**Output Transistor (Data)**

$V_{CE}$	Collector to Emitter Voltage
$V_{CB}$	Collector-to-Base Voltage
$V_{EC}$	Emitter-to-Collector Voltage
$P_D$	Power Dissipation at $T_A = 25^\circ\text{C}$ , $I_C$ (max) = 100 mA $V_{CE} = 1.5$ V Derate Linearly

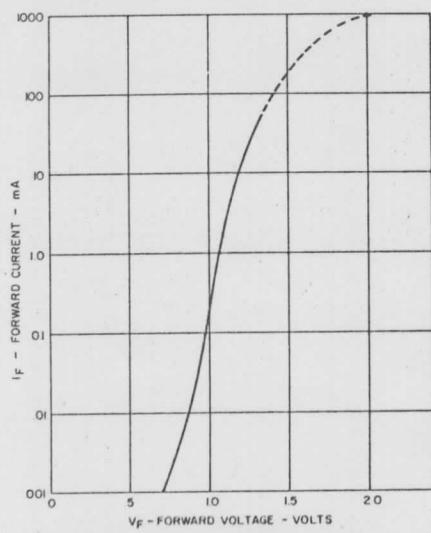
TYPICAL CHARACTERISTICS



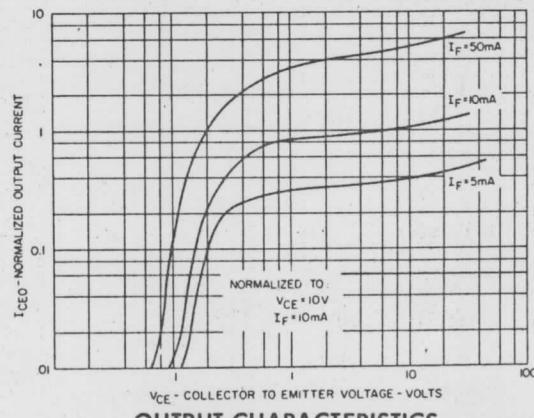
OUTPUT CURRENT VS INPUT CURRENT



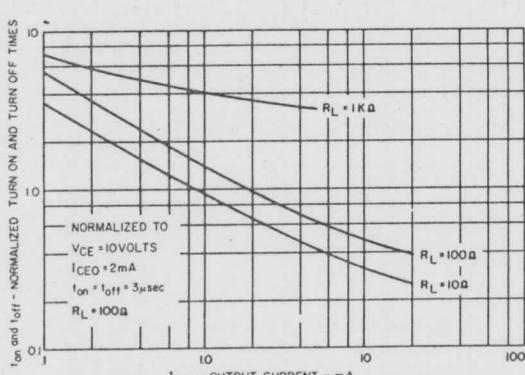
OUTPUT CURRENT VS TEMPERATURE



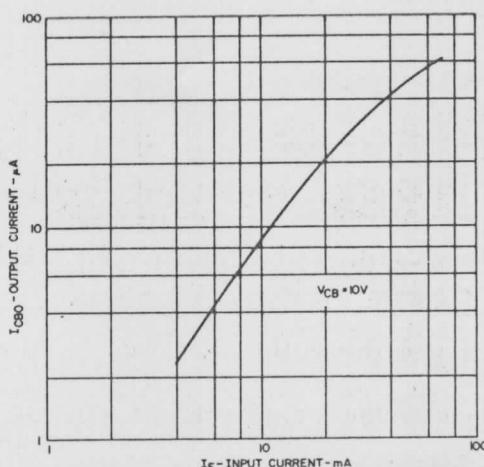
INPUT CHARACTERISTICS



OUTPUT CHARACTERISTICS



SWITCHING TIMES VS OUTPUT CURRENT



OUTPUT CURRENT ( $I_{CBO}$ ) VS INPUT CURRENT